

SSH9N80-VB Datasheet

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY

| | | |
|---|-----------------|------|
| V_{DS} (V) at T_J max. | 850 | |
| $R_{DS(on)}$ typ. (Ω) at 25 °C | $V_{GS} = 10$ V | 0.40 |
| Q_g max. (nC) | 88 | |
| Q_{gs} (nC) | 9 | |
| Q_{gd} (nC) | 16 | |
| Configuration | Single | |

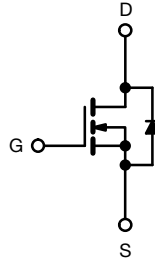
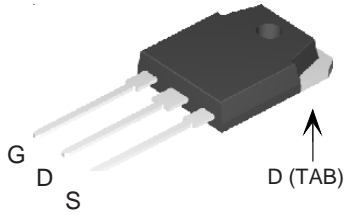
FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



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N-Channel MOSFET

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|------------------|----------------|------|
| Drain-source voltage | V_{DS} | 800 | V |
| Gate-source voltage | V_{GS} | ± 30 | |
| Continuous drain current ($T_J = 150$ °C) | V_{GS} at 10 V | $T_C = 25$ °C | 11 |
| | | $T_C = 100$ °C | 8 |
| Pulsed drain current ^a | I_{DM} | 32 | A |
| Linear derating factor | | 1.4 | W/°C |
| Single pulse avalanche energy ^b | E_{AS} | 226 | mJ |
| Maximum power dissipation | P_D | 179 | W |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C |
| Drain-source voltage slope | dV/dt | $T_J = 125$ °C | 70 |
| Reverse diode dV/dt ^d | | | 4.3 |
| Soldering recommendations (peak temperature) ^c | For 10 s | 300 | °C |


Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 4.0$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C

THERMAL RESISTANCE RATINGS

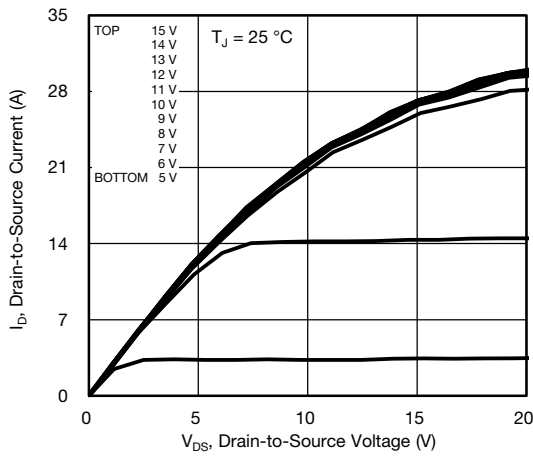
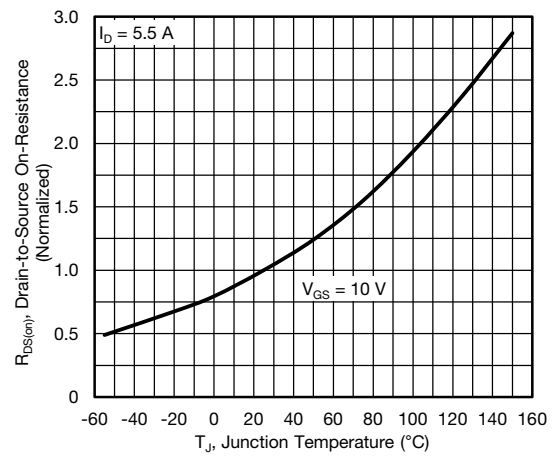
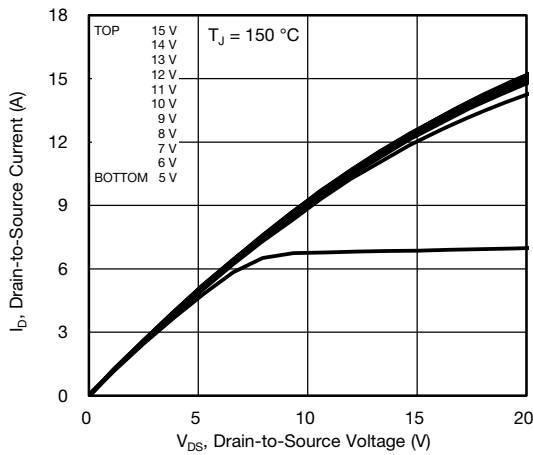
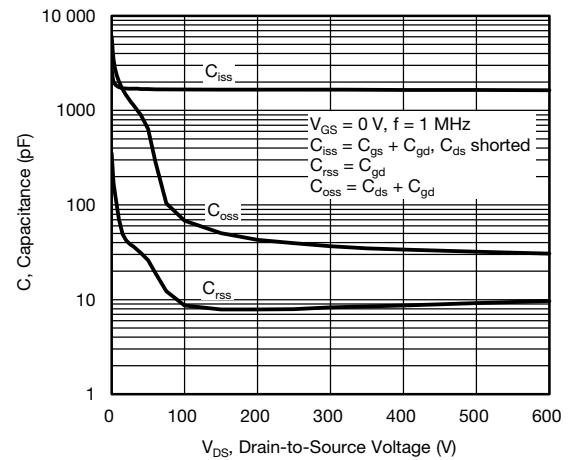
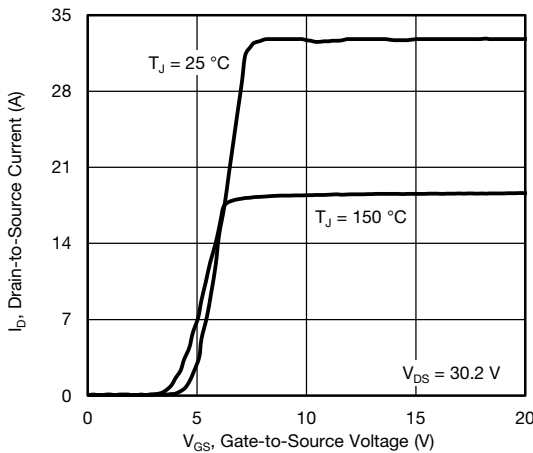
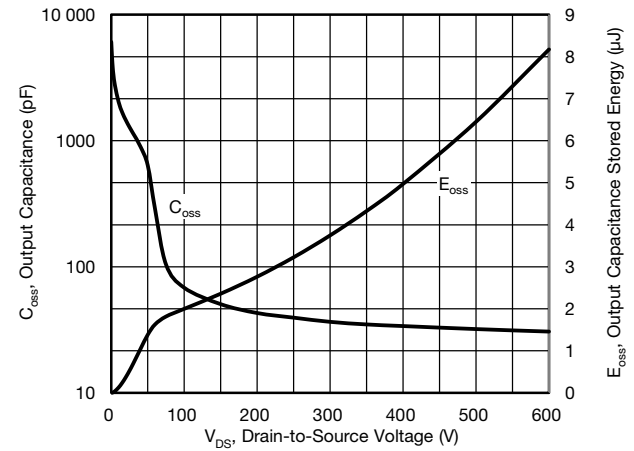
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum junction-to-ambient | R_{thJA} | - | 62 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | - | 0.7 | |

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|---------------------|--|--|------|------|-----------|---------------------|
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | | 800 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | | - | 1.1 | - | V/ $^\circ\text{C}$ |
| Gate-source threshold voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | | 2 | - | 4 | V |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| | | $V_{GS} = \pm 30\text{ V}$ | | - | - | ± 1 | μA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$ | | - | - | 1 | μA |
| | | $V_{DS} = 640\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ | | - | - | 10 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 5.5\text{ A}$ | - | 0.40 | - | Ω |
| Forward transconductance | g_{fs} | $V_{DS} = 30\text{ V}$, $I_D = 5.5\text{ A}$ | | - | 4.5 | - | S |
| Dynamic | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$ | | - | 1670 | - | pF |
| Output capacitance | C_{oss} | | | - | 68 | - | |
| Reverse transfer capacitance | C_{rss} | | | - | 9 | - | |
| Effective output capacitance, energy related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 480\text{ V}$, $V_{GS} = 0\text{ V}$ | | - | 43 | - | |
| Effective output capacitance, time related ^b | $C_{o(tr)}$ | | | - | 212 | - | |
| Total gate charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 5.5\text{ A}$, $V_{DS} = 480\text{ V}$ | - | 44 | 88 | nC |
| Gate-source charge | Q_{gs} | | | - | 9 | - | |
| Gate-drain charge | Q_{gd} | | | - | 16 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 480\text{ V}$, $I_D = 5.5\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$ | | - | 18 | 36 | ns |
| Rise time | t_r | | | - | 15 | 30 | |
| Turn-off delay time | $t_{d(off)}$ | | | - | 55 | 110 | |
| Fall time | t_f | | | - | 18 | 36 | |
| Gate input resistance | R_g | $f = 1\text{ MHz}$, open drain | | 0.4 | 0.9 | 1.8 | Ω |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 12 | A |
| Pulsed diode forward current | I_{SM} | | | - | - | 32 | |
| Diode forward voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}$, $I_S = 5.5\text{ A}$, $V_{GS} = 0\text{ V}$ | | - | - | 1.2 | V |
| Reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}$, $I_F = I_S = 5.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 25\text{ V}$ | | - | 345 | 690 | ns |
| Reverse recovery charge | Q_{rr} | | | - | 4.2 | 8.4 | μC |
| Reverse recovery current | I_{RRM} | | | - | 21 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

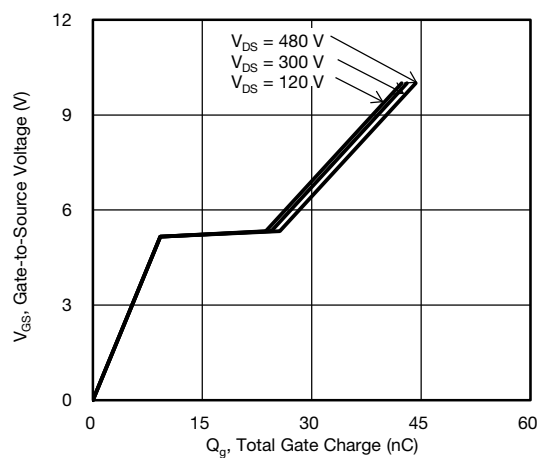


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

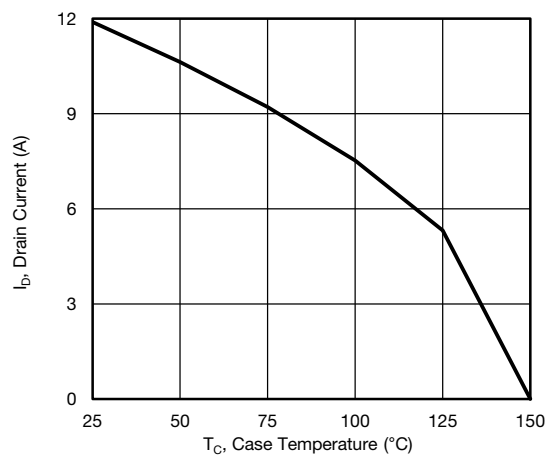


Fig. 10 - Maximum Drain Current vs. Case Temperature

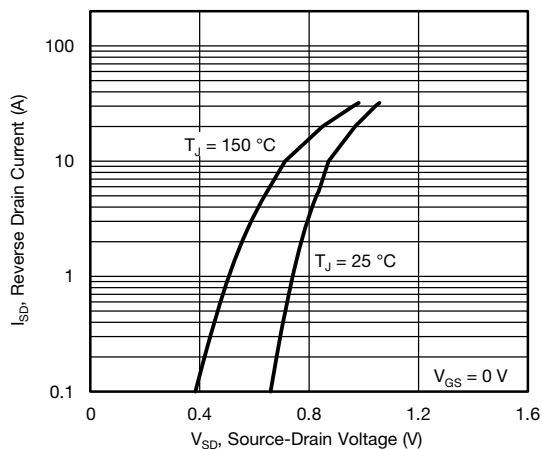


Fig. 8 - Typical Source-Drain Diode Forward Voltage

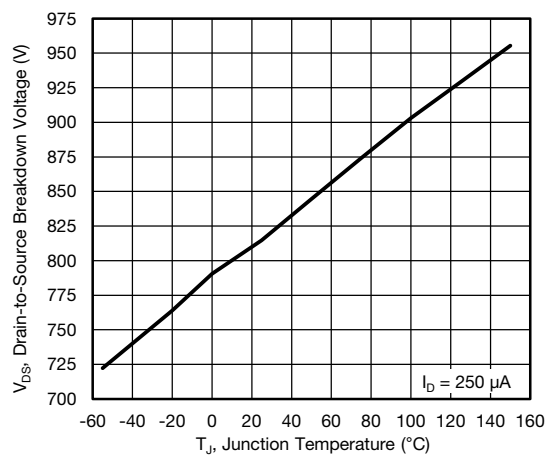


Fig. 11 - Temperature vs. Drain-to-Source Voltage

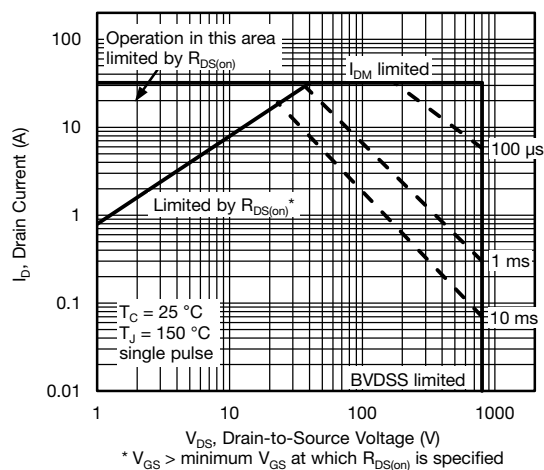
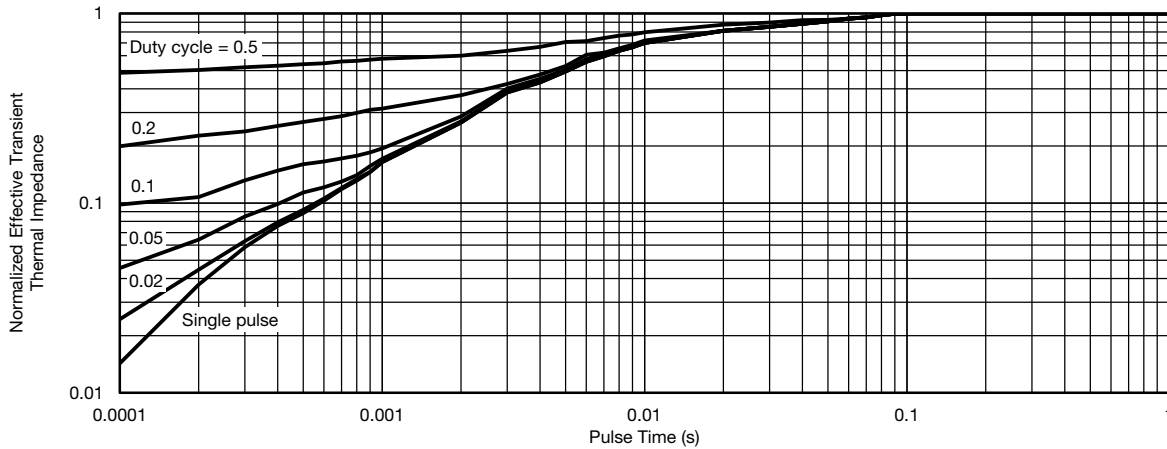
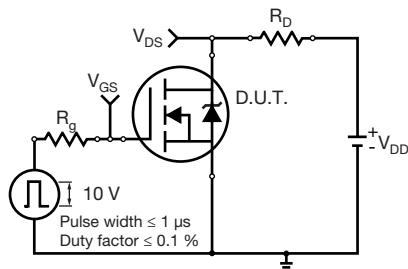
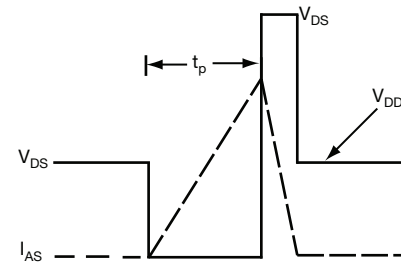
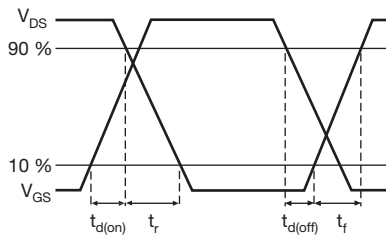
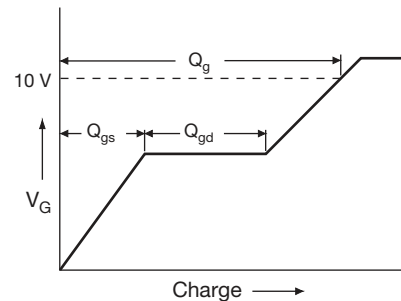
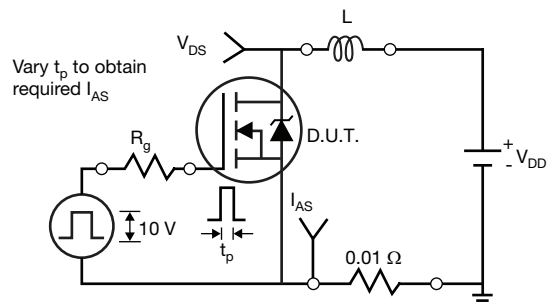
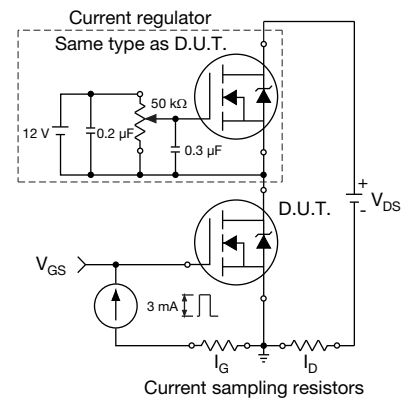


Fig. 9 - Maximum Safe Operating Area

* $V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit

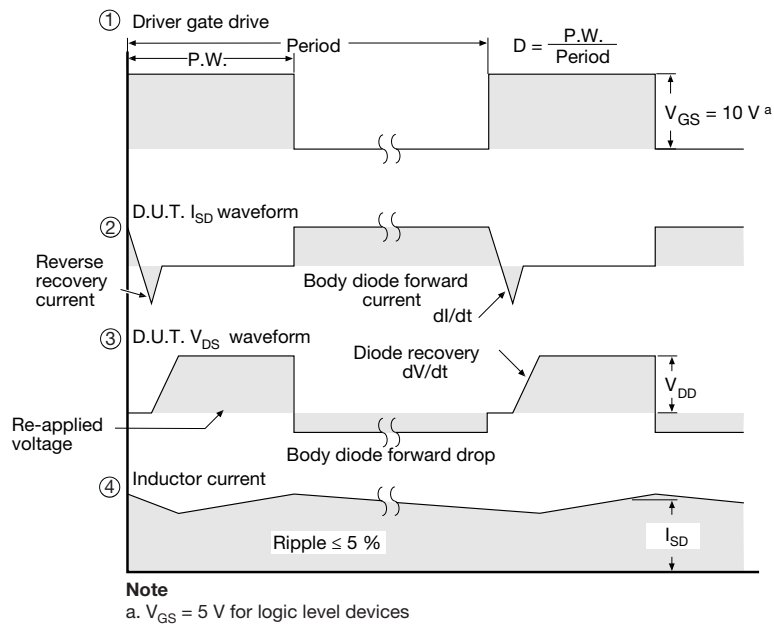
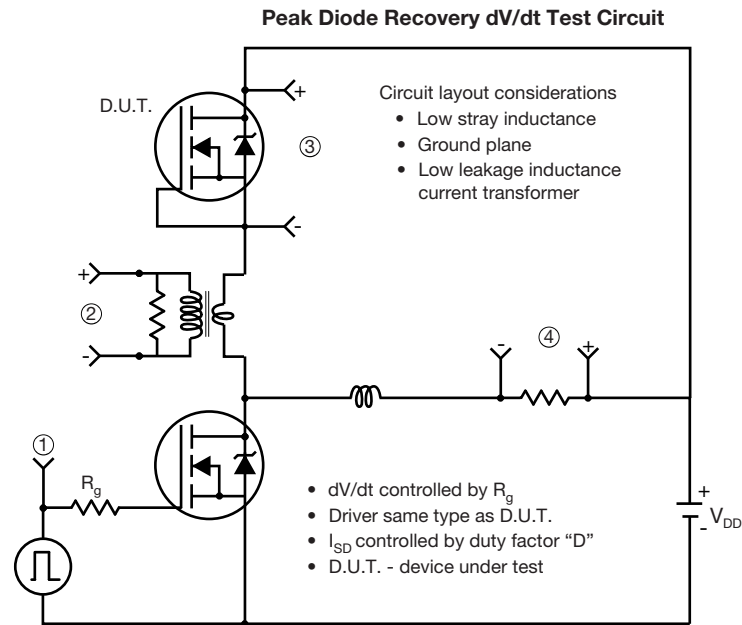
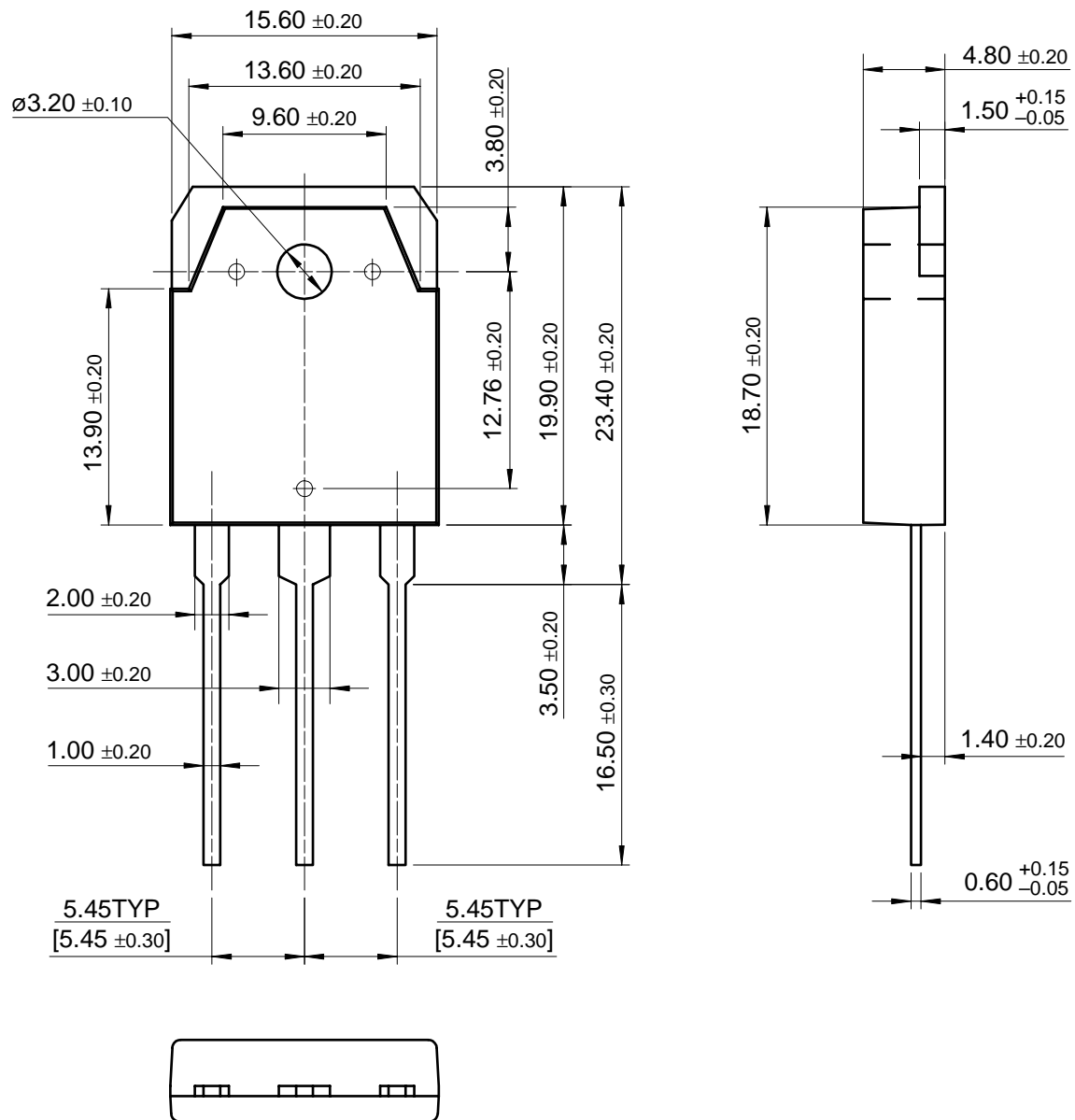


Fig. 19 - For N-Channel

TO-3P



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